

isc Silicon NPN Power Transistors

BUX82/83

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 400V(\text{Min})$ -BUX82
= $450V(\text{Min})$ -BUX83
- High Switching Speed

APPLICATIONS

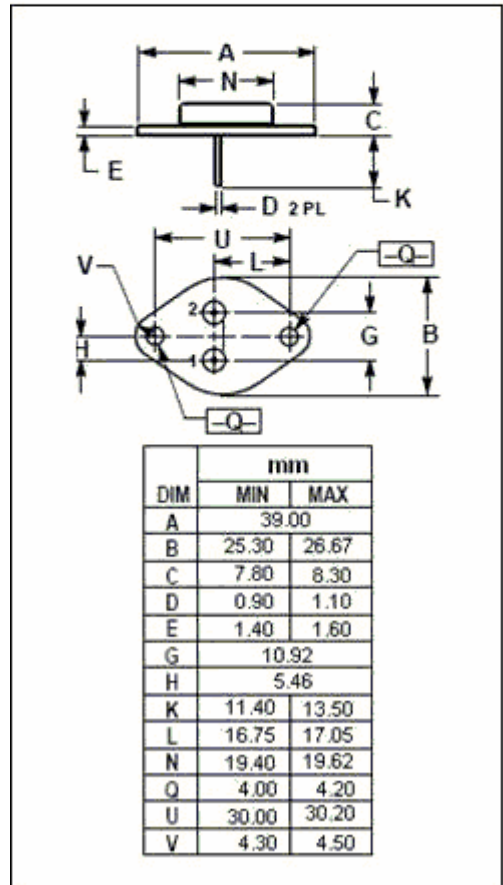
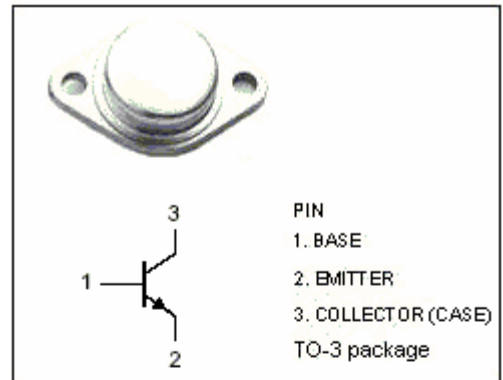
- Designed for use as high-speed power switch at high voltage.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CES}	Collector-Emitter Voltage	BUX82	800	V
		BUX83	1000	
V_{CEO}	Collector-Emitter Voltage	BUX82	400	V
		BUX83	450	
V_{CER}	Collector-Emitter Voltage $R_{BE} = 50\Omega$	BUX82	500	V
		BUX83	500	
V_{EBO}	Emitter-Base Voltage	10	V	
I_C	Collector Current-Continuous	6	A	
I_{CM}	Collector Current-Peak	8	A	
I_B	Base Current-Continuous	2	A	
I_{BM}	Base Current-Peak	3	A	
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	75	W	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.65	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	BUX82	$I_C=100\text{mA}; I_B=0; L=25\text{mH}$	400			V
		BUX83		450			
$V_{(BR)CER}$	Collector-Emitter Breakdown Voltage	BUX82	$I_C=100\text{mA}; R_{BE}=100\Omega; L=15\text{mH}$	500			V
		BUX83		500			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	BUX82	$I_C=4\text{A}; I_B=1.25\text{A}$			3.0	V
		BUX83				1.6	
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	BUX82	$I_C=2.5\text{A}; I_B=0.5\text{A}$			1.5	V
		BUX83				1.4	
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage		$I_C=4\text{A}; I_B=1.25\text{A}$			1.6	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage		$I_C=2.5\text{A}; I_B=0.5\text{A}$			1.4	V
I_{CES}	Collector Cutoff Current	BUX82	$V_{CES}=800\text{V}; V_{BE(off)}=1.5\text{V}$ $V_{CES}=800\text{V}; V_{BE(off)}=1.5\text{V}, T_C=125^{\circ}\text{C}$			1.0 2.0	mA
		BUX83		$V_{CES}=1000\text{V}; V_{BE(off)}=1.5\text{V}$ $V_{CES}=1000\text{V}; V_{BE(off)}=1.5\text{V}, T_C=125^{\circ}\text{C}$			
I_{EBO}	Emitter Cutoff Current		$V_{EB}=10\text{V}; I_C=0$			10	mA
h_{FE}	DC Current Gain		$I_C=1.2\text{A}; V_{CE}=5\text{V}$		30		
C_{OB}	Output Capacitance		$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$			500	pF
f_T	Current-Gain--Bandwidth Product		$I_C=0.2\text{A}; V_{CE}=10\text{V}; f_{test}=1\text{MHz}$		6		MHz

Switching Times

t_{on}	Turn-On Time	$I_C=2.5\text{A}; I_{B1}=0.5\text{A}; I_{B2}=-1\text{A}; V_{CC}=250\text{V}$		0.3	0.5	μs
t_{stg}	Storage Time			2.0	3.5	μs
t_f	Fall Time			0.3		μs